

#### 2-Phase Stepper-Motor Driver

**TLE4726G** 



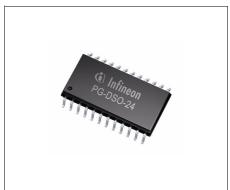


#### **Bipolar IC**

#### Overview

#### **Features**

- 2× 0.75 A / 50 V outputs
- Integrated driver, control logic and current control (chopper)
- Fast free-wheeling diodes
- Low standby-current drain
- Full, half, quarter, mini step



PG-DSO-24-13

Туре	Ordering Code	Package
TLE4726G	On Request	PG-DSO-24-13

#### **Description**

TLE4726G is a bipolar, monolithic IC for driving bipolar stepper motors, DC motors and other inductive loads that operate on constant current. The control logic and power output stages for two bipolar windings are integrated on a single chip which permits switched current control of motors with 0.75 A per phase at operating voltages up to 50 V.

The direction and value of current are programmed for each phase via separate control inputs. A common oscillator generates the timing for the current control and turn-on with phase offset of the two output stages. The two output stages in a full-bridge configuration have integrated, fast free-wheeling diodes and are free of crossover current. The logic is supplied either separately with 5 V or taken from the motor supply voltage by way of a series resistor and an integrated Z-diode. The device can be driven directly by a microprocessor with the possibility of all modes from full step through half step to mini step.

Data Sheet 1 Rev. 1.1, 2008-06-16



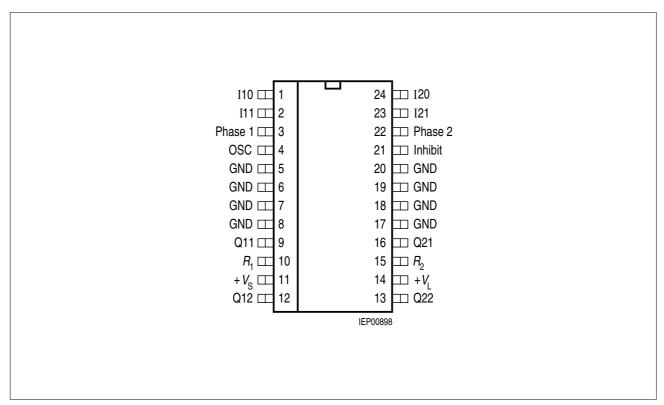


Figure 1 Pin Configuration (top view)

Data Sheet 2 Rev. 1.1, 2008-06-16



### **Pin Definitions and Functions**

Pin No.	Function	on						
1, 2, 23, 24	<b>Digital</b> particul		-	, <b>IX1</b> for the mag	nitude of the <b>current</b> of the			
	IX1	IX0	Phase Current	Example of Motor Status	_			
	Н	Н	0	No current				
	Н	L	1/3 $I_{\rm max}$	Hold	typical $I_{\text{max}}$ with			
	L	Н	2/3 I <sub>max</sub>	Set	$R_{\rm sense}$ = 1 $\Omega$ : 750 mA			
	L	L	$I_{max}$	Accelerate	_			
3		ntial the	phase curre	•	phase winding 1. On 1 to Q12, on L-potential in			
5, 6, 7, 8, 17, 18, 19, 20	Ground	<b>d</b> ; all pi	ns are conne	ected internally.				
4	Oscilla 2.2 nF.	tor; wo	rks at appro	x. 25 kHz if this p	in is wired to ground across			
10	Resiste	or $R_1$ fo	r sensing the	e current in phase	e 1.			
9, 12	Push-p diodes.		puts Q11, Q	12 for phase 1 w	ith integrated free-wheeling			
11		electroly	tic capacito		as possible to the IC, with a in parallel with a ceramic			
14	a series	s resisto groun	or. A Z-diode d directly on	of approx. 7 V is	V or connect to $+V_{\rm S}$ across integrated. In both cases ble electrolytic capacitor of 100 nF.			
13, 16	_	Push-pull outputs Q22, Q21 for phase 2 with integrated free-wheeling diodes.						
15	Resiste	or $R_2$ fo	r sensing the	e current in phase	e 2.			
21		Inhibit input; the IC can be put on standby by low potential on this pin. This reduces the current consumption substantially.						
22	H-pote	Input phase 2; controls the current flow through phase winding 2. On H-potential the phase current flows from Q21 to Q22, on L potential in the reverse direction.						

Data Sheet 3 Rev. 1.1, 2008-06-16



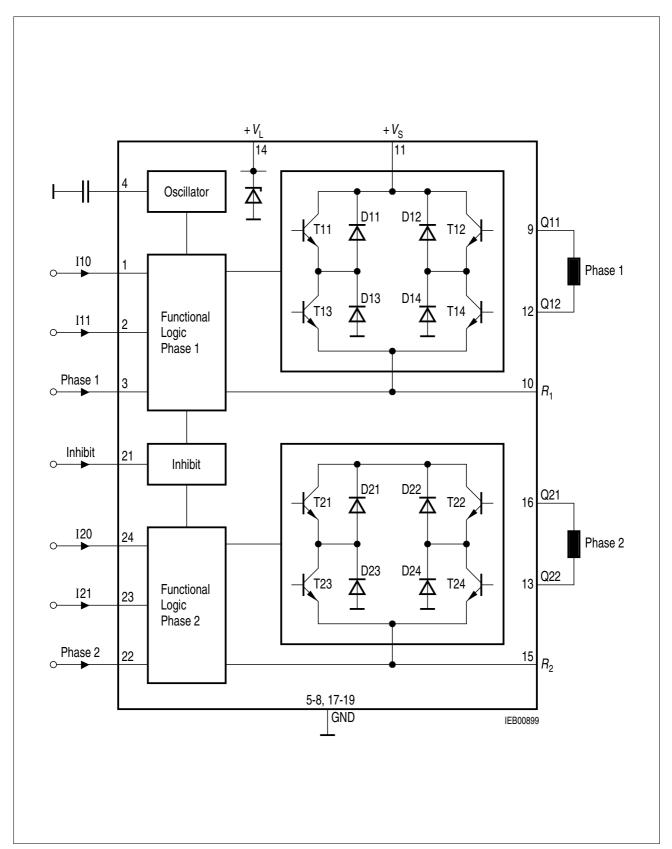


Figure 2 Block Diagram



### **Absolute Maximum Ratings**

 $T_{\rm A}$  = - 40 to 125  $^{\circ}{\rm C}$ 

Parameter	Symbol	Limit	Values	Unit	Remarks	
		min.	max.			
Supply voltage	$V_{S}$	0	52	V	_	
Logic supply voltage	$V_{L}$	0	6.5	V	Z-diode	
Z-current of $V_{L}$	$I_{L}$	_	50	mA	_	
Output current	$I_{Q}$	<b>– 1</b>	1	Α	_	
Ground current	$I_{GND}$	-2	2	Α	_	
Logic inputs	$V_{lxx}$	- 6	V <sub>L</sub> + 0.3	V	I <sub>XX</sub> ; Phase 1, 2; Inhibit	
$R_1, R_2$ , oscillator input voltage	$V_{RX,} \ V_{OSC}$	- 0.3	V <sub>L</sub> + 0.3	V	_	
Junction temperature	$T_{ m j} \ T_{ m j}$	-  -	125 150	°C °C	– max. 10,000 h	
Storage temperature	$T_{stg}$	- 50	125	°C	_	

Note: Stresses above those listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Data Sheet 5 Rev. 1.1, 2008-06-16



### **Operating Range**

Parameter	Symbol	Limit	Limit Values		Remarks
		min.	max.		
Supply voltage	$V_{S}$	5	50	V	_
Logic supply voltage	$V_{L}$	4.5	6.5	V	without series resistor
Case temperature	$T_{C}$	- 25	110	°C	measured on pin 5 $P_{\rm diss}$ = 2 W
Output current	$I_{Q}$	- 800	800	mA	_
Logic inputs	$V_{IXX}$	- 5	$V_{L}$	V	I <sub>XX</sub> ; Phase 1, 2; Inhibit

### **Thermal Resistances**

Junction ambien	t	R <sub>th ja</sub>	_	75	K/W	PG-DSO-24-13
Junction ambien	t (soldered on a 35 µm thick 20 cm² PC boar copper area)	$R_{thja}^{m,ja}$	_	50	K/W	PG-DSO-24-13
Junction case		$R_{thjc}$	_	15	K/W	measured on pin 5 PG-DSO-24-13

Note: In the operating range, the functions given in the circuit description are fulfilled.

### **Characteristics**

$$V_{\rm S}$$
 = 40 V;  $V_{\rm L}$  = 5 V;  $-$  25 °C  $\leq$   $T_{\rm j}$   $\leq$  125 °C   
Parameter Symbol Limit Values Unit Test Condition

Parameter	Symbol		Limit values		Unit	rest Condition
		min.	typ.	max.		
Current Consum	ption					
$\overline{\text{from} + V_{\text{S}}}$	$I_{\mathbb{S}}$	_	0.2	0.5	mA	$V_{inh} = L$
from + $V_{\rm S}$	$I_{S}$	_	16	20	mA	$\begin{aligned} V_{\text{inh}} &= L \\ V_{\text{inh}} &= H \\ I_{\text{Q1/2}} &= 0,  I_{\text{XX} = L} \\ V_{\text{inh}} &= L \end{aligned}$
						$I_{Q1/2} = 0, I_{XX = L}$
from + $V_{L}$	$ I_L $	-	1.7	3	mA	$V_{inh} = L$
from + $V_{L}$	$I_{L}$	_	18	25	mA	$V_{inh} = H$
						$V_{\text{inh}}^{} = H$ $I_{\text{Q1/2}} = 0, I_{\text{XX} = L}$

Data Sheet 6 Rev. 1.1, 2008-06-16



### Characteristics (cont'd)

 $V_{\mathrm{S}}$  = 40 V;  $V_{\mathrm{L}}$  = 5 V; - 25 °C  $\leq$   $T_{\mathrm{j}}$   $\leq$  125 °C

Parameter	Symbol	Symbol Limit Values			Unit	<b>Test Condition</b>
		min.	typ.	max.		
Oscillator				-		1
Output charging current	$I_{OSC}$	_	110	_	μΑ	_
Charging threshold	$V_{OSCL}$	_	1.3	-	V	_
Discharging threshold	$V_{OSCH}$	_	2.3	-	V	_
Frequency	$f_{\sf OSC}$	18	25	40	kHz	$C_{\rm OSC} = 2.2 \; {\rm nF}$

### Phase Current Selection Current Limit Threshold

No current	$V_{sensen}$	_	0	_	mV	IX0 = H; IX1 = H
Hold	$V_{senseh}$	200	250	300	mV	IX0 = L; IX1 = H
Setpoint	$V_{sense s}$	420	540	680	mV	IX0 = H; IX1 = L
Accelerate	$V_{sensea}$	700	825	950	mV	IX0 = L; IX1 = L

## **Logic Inputs**

 $(I_{X1}; I_{X0}; Phase x)$ 

Threshold	$\mid V_1 \mid$	1.4  -	2.3	V	-
	'	(H→L)	(L→H)		
L-input current	$I_{IL}$	<b>– 10 –</b>	_	μA	$V_{\rm I} = 1.4 \ { m V}$
L-input current	$I_{IL}$	- 100  -	_	μA	$V_{I} = O V$
H-input current	$I_{IH}$	-  -	10	μΑ	$V_{I} = 5 V$

## **Standby Cutout (inhibit)**

Threshold	$V_{Inh}$	2	3	4	V	_
	(L→H)					
Threshold	$V_{Inh}$	1.7	2.3	2.9	V	_
	(H→L)					
Hysteresis	$V_{Inhhy}$	0.3	0.7	1.1	V	_

### **Internal Z-Diode**

Z-voltage	$V_{LZ}$	6.5	7.4	8.2	V	$I_{\rm L}$ = 50 mA

Data Sheet 7 Rev. 1.1, 2008-06-16



### **Characteristics** (cont'd)

 $V_{\rm S}$  = 40 V;  $V_{\rm L}$  = 5 V; - 25 °C  $\leq$   $T_{\rm j}$   $\leq$  125 °C

Parameter	Symbol	Limit Values			Unit	Test Condition
		min.	typ.	max.		

### **Power Outputs**

# **Diode Transistor Sink Pair**

(D13, T13; D14, T14; D23, T23; D24, T24)

Saturation voltage	$V_{satl}$	_	0.3	0.6	V	$I_{\rm O} = -0.5  {\rm A}$
Saturation voltage	$V_{satl}$	_	0.5	1	V	$I_{\rm Q} = -0.75  {\rm A}$
Reverse current	$I_{RI}$	_	_	300	μΑ	$V_{\rm Q}$ = 40 V
Forward voltage	$V_{FI}$	_	0.9	1.3	V	$I_{\rm Q} = 0.5 {\rm A}$
Forward voltage	$V_{FI}$	_	1	1.4	V	$I_{\rm Q} = 0.75 \; {\rm A}$

## **Diode Transistor Source Pair**

(D11, T11; D12, T12; D21, T21; D22, T22)

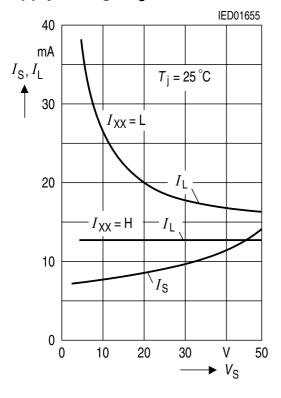
Saturation voltage	$V_{satuC}$	_	0.9	1.2	V	$I_{\rm Q} = 0.5 \text{ A};$
0	17		0.0	0.7	.,	charge
Saturation voltage	$V_{satuD}$	_	0.3	0.7	V	$I_{\rm Q}$ = 0.5 A; discharge
Saturation voltage	$V_{satuC}$	_	1.1	1.4	V	$I_{\rm O} = 0.75 \text{ A};$
· ·	Janus					charge
Saturation voltage	$V_{satuD}$	_	0.5	1	V	$I_{\rm Q} = 0.75 \text{ A};$
						discharge
Reverse current	$I_{Ru}$	_	_	300	μΑ	$V_{Q} = 0 \; V$
Forward voltage	$V_{Fu}$	_	1	1.3	V	$I_{\rm O} = -0.5  {\rm A}$
Forward voltage	$V_{Fu}$	_	1.1	1.4	V	$I_{\rm Q} = -0.75  {\rm A}$
Diode leakage current	$I_{SL}$	_	1	2	mA	$I_{\rm F} = -0.75 \; {\rm A}$

Note: The listed characteristics are ensured over the operating range of the integrated circuit. Typical characteristics specify mean values expected over the production spread. If not otherwise specified, typical characteristics apply at  $T_A = 25\,^{\circ}\text{C}$  and the given supply voltage.

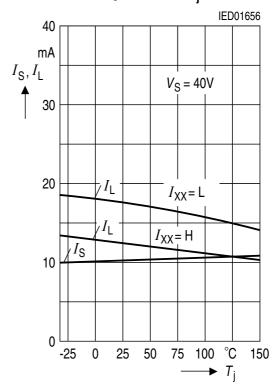
Data Sheet 8 Rev. 1.1, 2008-06-16



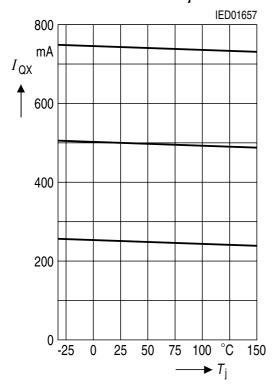
# Quiescent Current $I_{\rm S}, I_{\rm L}$ versus Supply Voltage $V_{\rm S}$



# Quiescent Current $I_{\rm S}, I_{\rm L}$ versus Junction Temperature $T_{\rm i}$



# Output Current $I_{QX}$ versus Junction Temperature $T_{\rm j}$



### **Operating Condition:**

 $V_{\text{L}} = 5 \text{ V}$  $V_{\text{Inh}} = \text{H}$ 

 $C_{\rm OSC}$  = 2.2 nF

 $R_{\rm sense} = 1 \Omega$ 

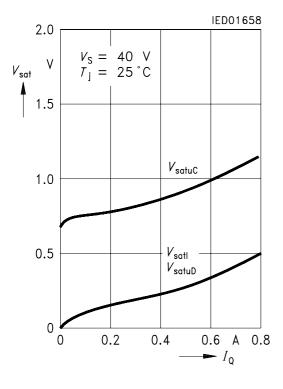
Load: L = 10 mH

 $R = 2.4 \Omega$ 

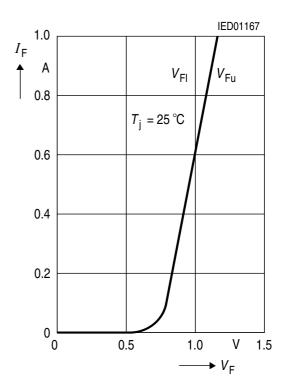
 $f_{\text{phase}} = 50 \text{ Hz}$ mode: fullstep



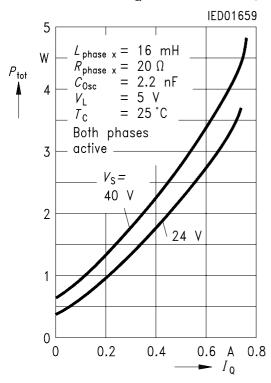
# Output Saturation Voltages $V_{\rm sat}$ versus Output Current $I_{\rm Q}$



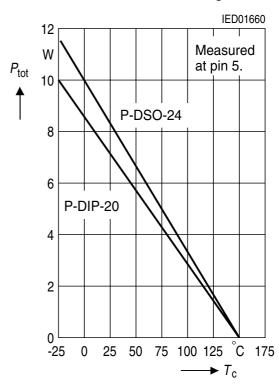
# Forward Current $I_{\rm F}$ of Free-Wheeling Diodes versus Forward Voltages $V_{\rm F}$



# Typical Power Dissipation $P_{\text{tot}}$ versus Output Current $I_{\text{Q}}$ (Non Stepping)

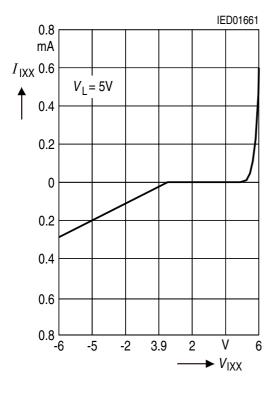


# Permissible Power Dissipation $P_{\mathrm{tot}}$ versus Case Temperature $T_{\mathrm{C}}$

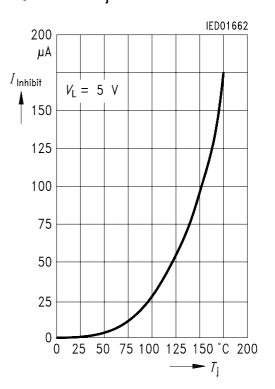




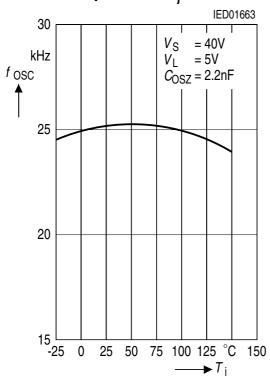
# Input Characteristics of $I_{\rm xx}$ , Phase X, Inhibit



# Input Current of Inhibit versus Junction Temperature $T_{\rm i}$



# Oscillator Frequency $f_{\rm OSC}$ versus Junction Temperature $T_{\rm j}$





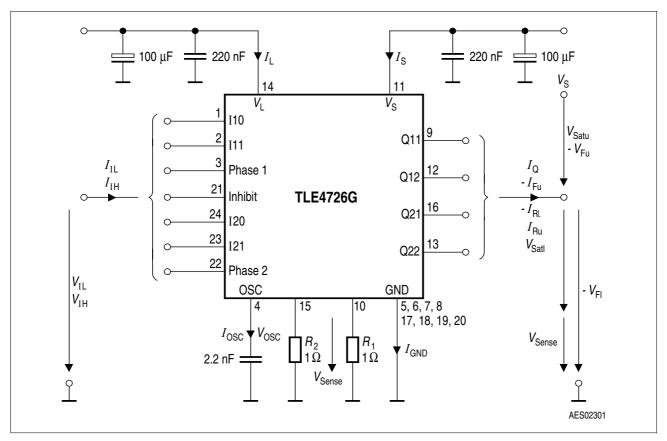


Figure 3 Test Circuit

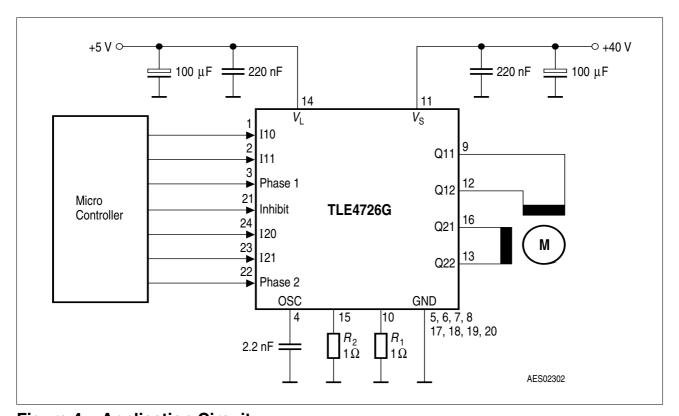


Figure 4 Application Circuit



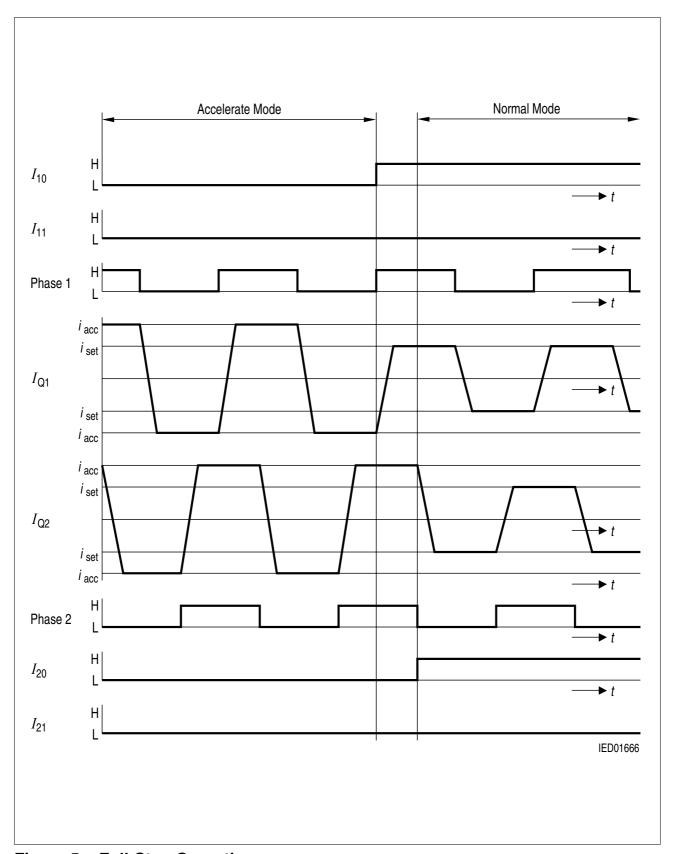


Figure 5 Full-Step Operation



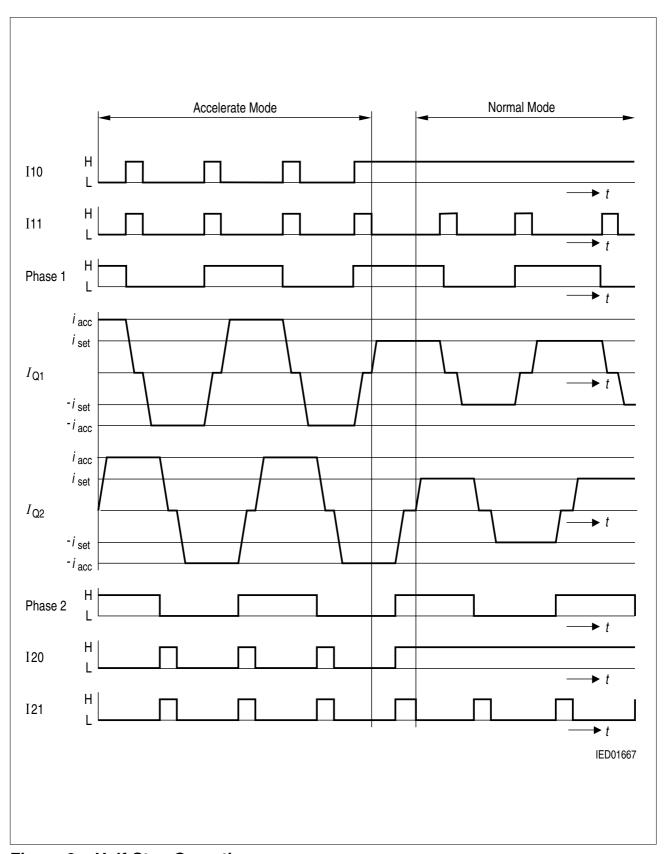


Figure 6 Half-Step Operation



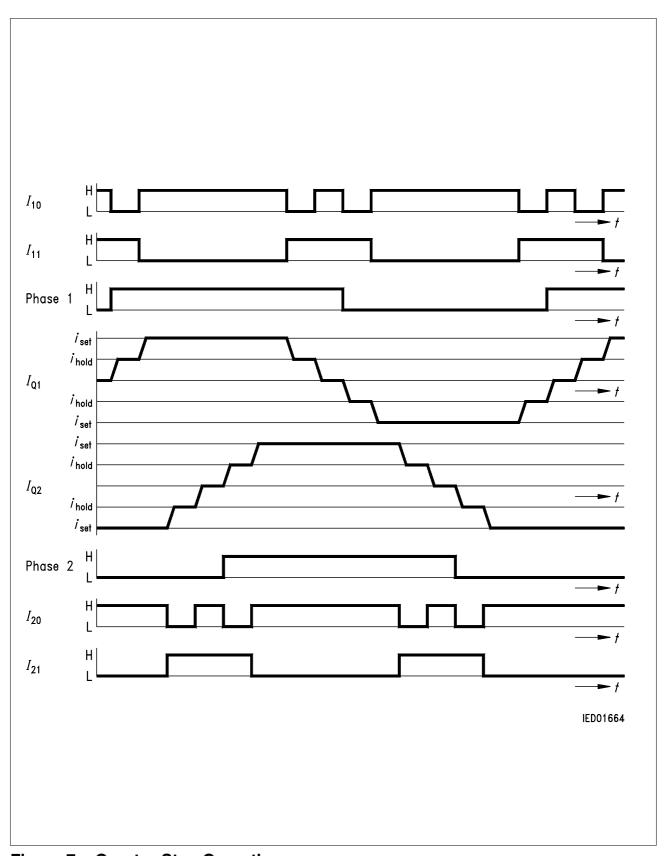


Figure 7 Quarter-Step Operation



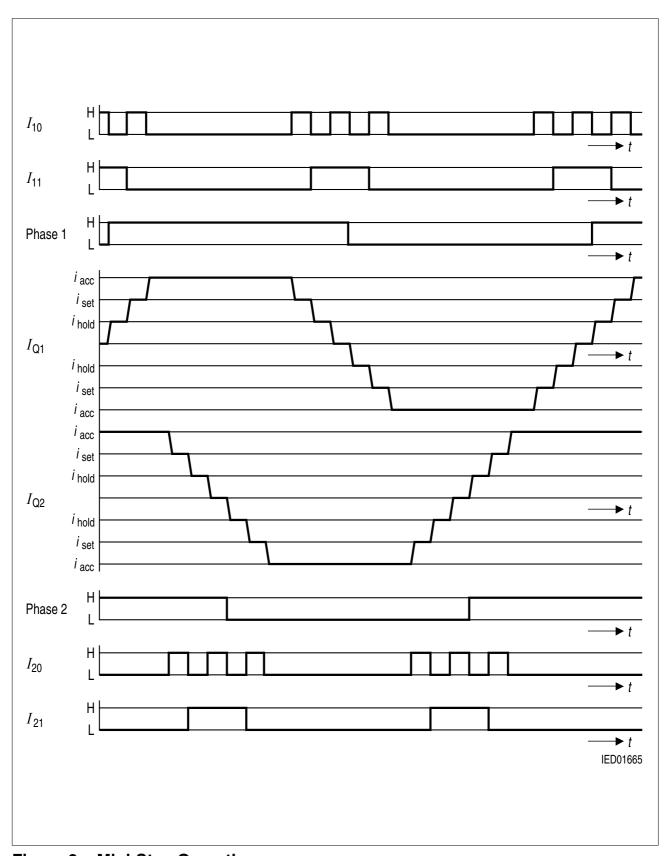


Figure 8 Mini-Step Operation



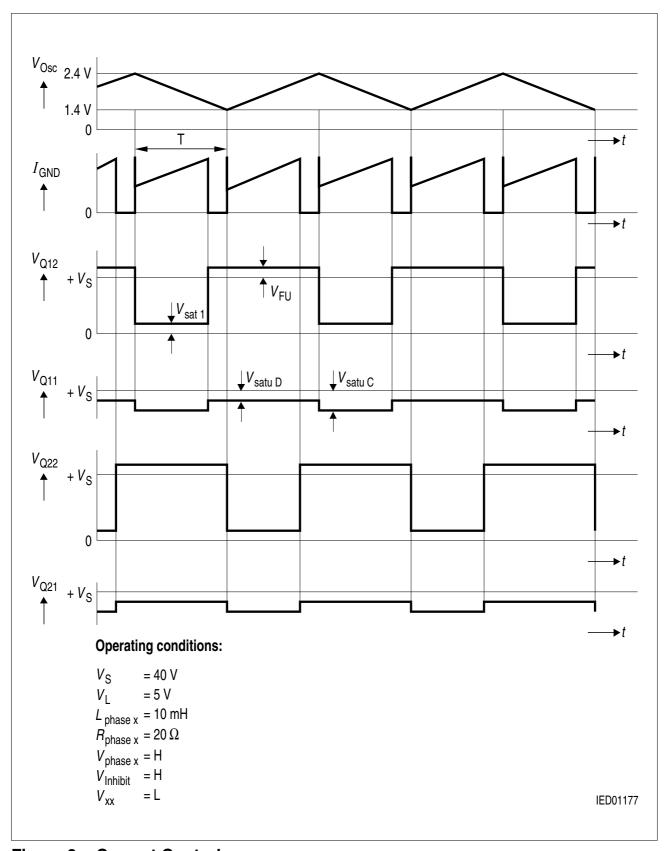


Figure 9 Current Control



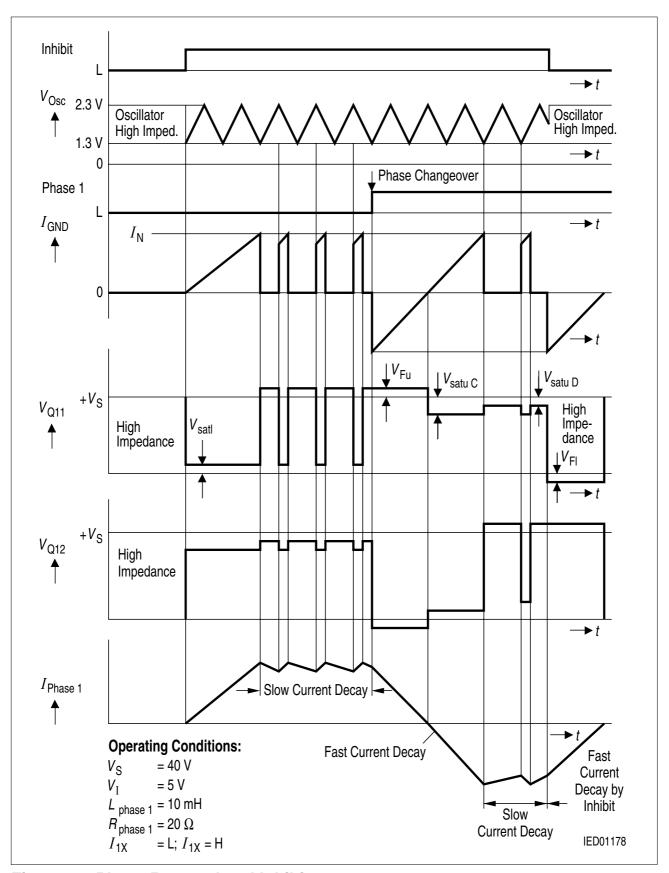


Figure 10 Phase Reversal and Inhibit



### **Calculation of Power Dissipation**

The total power dissipation  $P_{\text{tot}}$  is made up of

**saturation losses**  $P_{\rm sat}$  (transistor saturation voltage and diode forward voltages), **quiescent losses**  $P_{\rm q}$  (quiescent current times supply voltage) and **switching losses**  $P_{\rm s}$  (turn-ON / turn-OFF operations).

The following equations give the power dissipation for chopper operation without phase reversal. This is the worst case, because full current flows for the entire time and switching losses occur in addition.

$$\begin{split} P_{\text{tot}} &= 2 \times P_{\text{sat}} + P_{\text{q}} + 2 \times P_{\text{s}} \\ \text{where} \qquad P_{\text{sat}} &\cong I_{\text{N}} \left\{ \left. V_{\text{satl}} \times d + V_{\text{Fu}} \left( 1 - d \right) + V_{\text{satuC}} \times d + V_{\text{satuD}} \left( 1 - d \right) \right. \right\} \\ P_{\text{q}} &= I_{\text{q}} \times V_{\text{S}} + I_{\text{L}} \times V_{\text{L}} \\ P_{\text{S}} &\cong \frac{V_{\text{S}}}{T} \left\{ \frac{i_{\text{D}} \times t_{\text{DON}}}{2} + \frac{i_{\text{D}} + i_{\text{R}} \times t_{\text{ON}}}{4} + \frac{I_{\text{N}}}{2} t_{\text{DOFF}} + t_{\text{OFF}} \right\} \end{split}$$

 $I_{N}$  = nominal current (mean value)

 $I_{\alpha}$  = quiescent current

 $i_D$  = reverse current during turn-on delay

 $i_{\rm R}$  = peak reverse current

 $t_{\rm p}$  = conducting time of chopper transistor

 $t_{\text{ON}}$  = turn-ON time  $t_{\text{OFF}}$  = turn-OFF time  $t_{\text{DON}}$  = turn-ON delay  $t_{\text{DOFF}}$  = turn-OFF delay T = cycle duration d = duty cycle  $t_{\text{p}}/T$ 

 $V_{\text{satt}}$  = saturation voltage of sink transistor (T3, T4)

 $V_{\rm satuC}$  = saturation voltage of source transistor (T1, T2) during charge cycle  $V_{\rm satuD}$  = saturation voltage of source transistor (T1, T2) during discharge cycle

 $V_{\text{Fu}}$  = forward voltage of free-wheeling diode (D1, D2)

 $egin{array}{ll} V_{\mathrm{S}} &= \mathrm{supply} \ \mathrm{voltage} \ V_{\mathrm{L}} &= \mathrm{logic} \ \mathrm{supply} \ \mathrm{voltage} \ I_{\mathrm{L}} &= \mathrm{current} \ \mathrm{from} \ \mathrm{logic} \ \mathrm{supply} \ \end{array}$ 



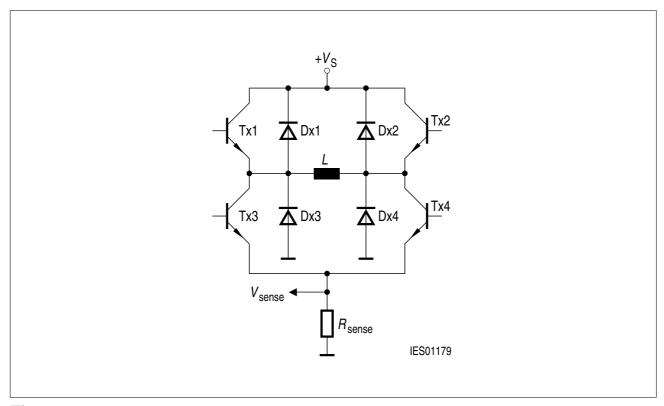


Figure 11

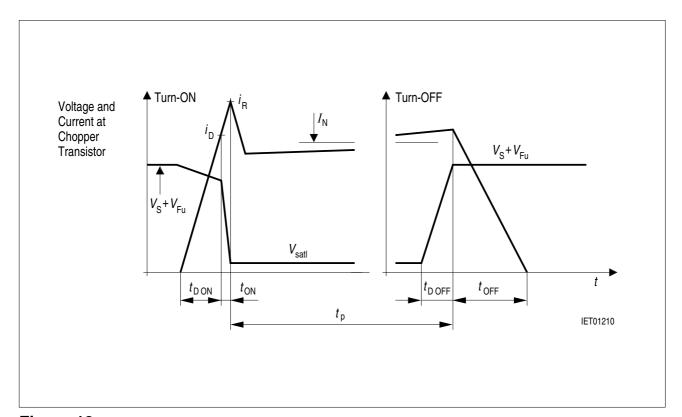


Figure 12



### **Application Hints**

The TLE726G is intended to drive both phases of a stepper motor. Special care has been taken to provide high efficiency, robustness and to minimize external components.

### **Power Supply**

The TLE726G will work with supply voltages ranging from 5 V to 50 V at pin  $V_{\rm S}$ . As the circuit operates with chopper regulation of the current, interference generation problems can arise in some applications. Therefore the power supply should be decoupled by a 0.22  $\mu F$  ceramic capacitor located near the package. Unstabilized supplies may even afford higher capacities.

### **Current Sensing**

The current in the windings of the stepper motor is sensed by the voltage drop across  $R_1$  and  $R_2$ . Depending on the selected current internal comparators will turn off the sink transistor as soon as the voltage drop reaches certain thresholds (typical 0 V, 0.25 V, 0.5 V and 0.75 V); ( $R_1$ ,  $R_2$  = 1  $\Omega$ ). These thresholds are neither affected by variations of  $V_L$  nor by variations of  $V_S$ .

Due to chopper control fast current rises (up to 10 A/ $\mu$ s) will occur at the sensing resistors  $R_1$  and  $R_2$ . To prevent malfunction of the current sensing mechanism  $R_1$  and  $R_2$  should be pure ohmic. The resistors should be wired to GND as directly as possible. Capacitive loads such as long cables (with high wire to wire capacity) to the motor should be avoided for the same reason.

### **Synchronizing Several Choppers**

In some applications synchrone chopping of several stepper motor drivers may be desireable to reduce acoustic interference. This can be done by forcing the oscillator of the TLE726G by a pulse generator overdriving the oscillator loading currents (approximately  $\pm$  100  $\mu A$ ). In these applications low level should be between 0 V and 1 V while high level should be between 2.6 V and  $V_{\rm I}$ .

### **Optimizing Noise Immunity**

Unused inputs should always be wired to proper voltage levels in order to obtain highest possible noise immunity.

To prevent crossconduction of the output stages the TLE4726G uses a special break before make timing of the power transistors. This timing circuit can be triggered by short glitches (some hundred nanoseconds) at the Phase inputs causing the output stage to become high resistive during some microseconds. This will lead to a fast current decay during that time. To achieve maximum current accuracy such glitches at the Phase inputs should be avoided by proper control signals.

Data Sheet 21 Rev. 1.1, 2008-06-16



#### **Thermal Shut Down**

To protect the circuit against thermal destruction, thermal shut down has been implemented. To provide a warning in critical applications, the current of the sensing element is wired to input Inhibit. Before thermal shut down occurs Inhibit will start to pull down by some hundred microamperes. This current can be sensed to build a temperature prealarm.

Data Sheet 22 Rev. 1.1, 2008-06-16



**Package Outlines** 

### 1 Package Outlines

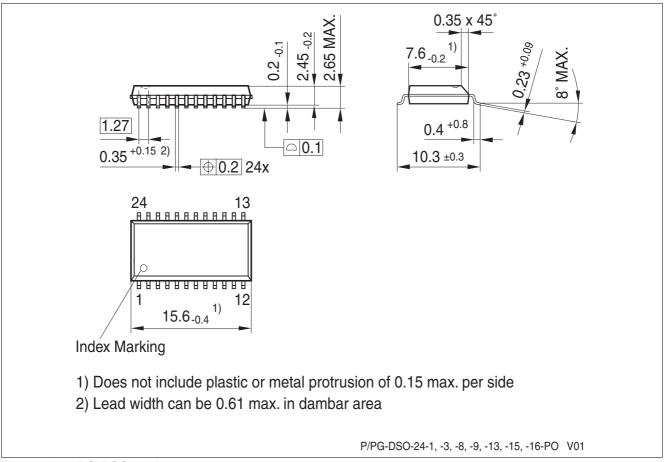


Figure 1 PG-DSO-24-13

#### **Green Product (RoHS compliant)**

To meet the world-wide customer requirements for environmentally friendly products and to be compliant with government regulations the device is available as a green product. Green products are RoHS-Compliant (i.e Pb-free finish on leads and suitable for Pb-free soldering according to IPC/JEDEC J-STD-020).



**Revision History** 

# 2 Revision History

Revision	Date	Changes
1.1 2008-06-17		Initial version of RoHS-compliant derivate of TLE4726
		Page 1: AEC certified statement added
		Page 1 and 23: added RoHS compliance statement and Green product feature
		Page 1 and 23: Package changed to RoHS compliant version
		Page 24-25: added Revision History, updated Legal Disclaimer

Edition 2008-01-04

Published by Infineon Technologies AG 81726 Munich, Germany © 2008 Infineon Technologies AG All Rights Reserved.

#### **Legal Disclaimer**

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

#### Information

For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office (www.infineon.com).

#### Warnings

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office.

Infineon Technologies components may be used in life-support devices or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

# **Mouser Electronics**

**Authorized Distributor** 

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Infineon: